PD- 95141

International
IOR Rectifier

IRFPS40N50LPbF

SMPS MOSFET

HEXFET® Power MOSFET

V_{DSS}	$R_{DS(on)}$ typ.	Trr typ.	I_D
500V	0.087Ω	170ns	46A

Applications

- Zero Voltage Switching SMPS
- Telecom and Server Power Supplies
- Uninterruptible Power Supplies
- Motor Control applications
- Lead-Free

Features and Benefits

- SuperFast body diode eliminates the need for external diodes in ZVS applications.
- Lower Gate charge results in simpler drive requirements.
- Enhanced dv/dt capabilities offer improved ruggedness.
- Higher Gate voltage threshold offers improved noise immunity.

Super-247™

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	46	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	29	
I_{DM}	Pulsed Drain Current ①	180	
P_D @T_C = 25°C	Power Dissipation	540	W
	Linear Derating Factor	4.3	W/°C
V_{GS}	Gate-to-Source Voltage	±30	V
dv/dt	Peak Diode Recovery dv/dt ②	34	V/ns
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	46	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	180		
V_{SD}	Diode Forward Voltage	—	—	1.5	V	T_J = 25°C, I_S = 46A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	170	250	ns	T_J = 25°C, I_F = 46A
		—	220	330		T_J = 125°C, di/dt = 100A/µs ④
Q_{rr}	Reverse Recovery Charge	—	705	1060	nC	T_J = 25°C, I_S = 46A, V_{GS} = 0V ④
		—	1.3	2.0		T_J = 125°C, di/dt = 100A/µs ④
I_{RRM}	Reverse Recovery Current	—	9.0	—	A	T_J = 25°C
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Static @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.60	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.087	0.100	Ω	V_{GS} = 10V, I_D = 28A ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	V_{DS} = V_{GS}, I_D = 250µA
I_{DSS}	Drain-to-Source Leakage Current	—	—	50	µA	V_{DS} = 500V, V_{GS} = 0V
		—	—	2.0	mA	V_{DS} = 400V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 30V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -30V
R_G	Internal Gate Resistance	—	0.90	—	Ω	f = 1MHz, open drain

Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	21	—	—	S	V_{DS} = 50V, I_D = 46A
Q_g	Total Gate Charge	—	—	380	nC	I_D = 46A
Q_{gs}	Gate-to-Source Charge	—	—	80		V_{DS} = 400V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	190		V_{GS} = 10V, See Fig. 7 & 15 ④
$t_{d(on)}$	Turn-On Delay Time	—	27	—	ns	V_{DD} = 250V
t_r	Rise Time	—	170	—		I_D = 46A
$t_{d(off)}$	Turn-Off Delay Time	—	50	—		R_G = 0.85Ω
t_f	Fall Time	—	69	—		V_{GS} = 10V, See Fig. 14a & 14b ④
C_{iss}	Input Capacitance	—	8110	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	960	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	130	—		f = 1.0MHz, See Fig. 5
C_{oss}	Output Capacitance	—	11200	—		V_{GS} = 0V, VDS = 1.0V, f = 1.0MHz
C_{oss}	Output Capacitance	—	240	—		V_{GS} = 0V, VDS = 400V, f = 1.0MHz
C_{oss} eff.	Effective Output Capacitance	—	440	—		V_{GS} = 0V,V_{DS} = 0V to 400V ⑤
C_{oss} eff. (ER)	Effective Output Capacitance (Energy Related)	—	310	—		

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	920	mJ
I_{AR}	Avalanche Current ①	—	46	A
E_{AR}	Repetitive Avalanche Energy ①	—	54	mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case⑥	—	0.23	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient⑥	—	40	

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See Fig. 11).

② Starting T_J = 25°C, L = 0.86mH, R_G = 25Ω, I_{AS} = 46A. (See Figure 12).

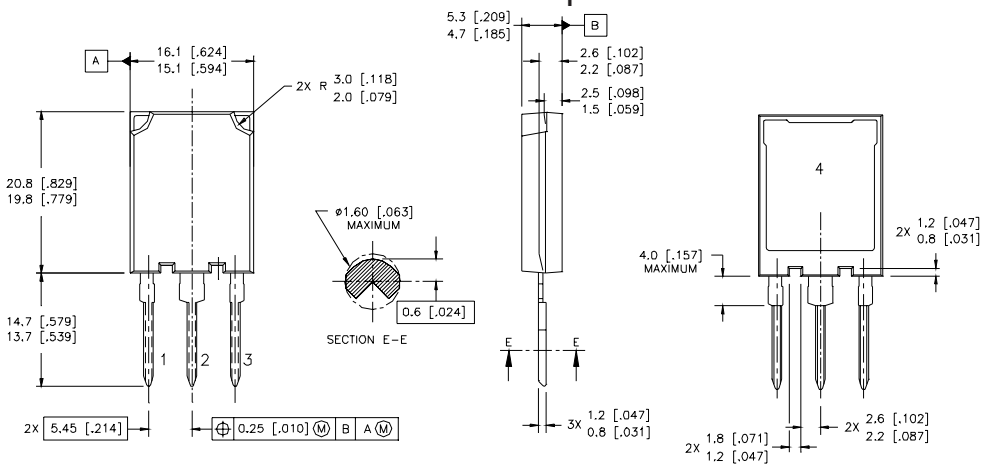
③ I_{SD} ≤ 46A, di/dt ≤ 550A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150°C.

④ Pulse width ≤ 400µs; duty cycle ≤ 2%.

⑤ C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
C_{oss} eff.(ER) is a fixed capacitance that stores the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

⑥ R_θ is measured at T_J approximately 90°C

Case Outline and Dimensions — Super-247



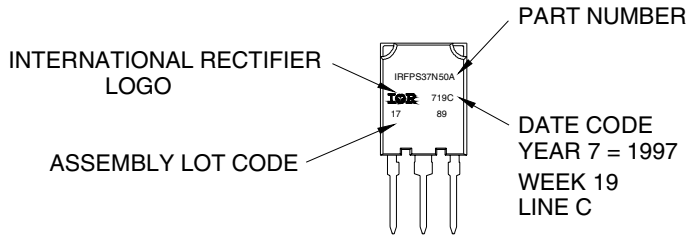
NOTES:
1. DIMENSIONS & TOLERANCING PER ASME Y14.5M-1994
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETRES [INCHES]

LEAD ASSIGNMENTS

MOSFET	IGBT
1 – GATE	1 – GATE
2 – DRAIN	2 – COLLECTOR
3 – SOURCE	3 – EMITTER
4 – DRAIN	4 – COLLECTOR

Super-247 (TO-274AA) Part Marking Information

EXAMPLE: THIS IS AN IRFPS37N50A WITH
ASSEMBLY LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



Note: "P" in assembly line position indicates "Lead-Free"

This product has been designed and qualified for the industrial market.
Qualification Standards can be found on IR's Web site.